

1. General description

Planar passivated very sensitive gate Silicon Controlled Rectifier in a TO92 plastic package.

2. Features and benefits

- Planar passivated for voltage ruggedness and reliability
- Very sensitive gate

3. Applications

- Ignition circuits
- Low power latching circuits
- Protection / shut-down circuits: lighting ballasts
- Protection / shut-down circuits: Switched Mode Power Supplies

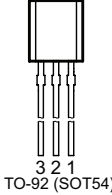

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Absolute maximum rating						
V_{RRM}	repetitive peak reverse voltage		-	-	400	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{lead} \leq 83\text{ °C}$; Fig. 1	-	-	0.5	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{lead} \leq 83\text{ °C}$; Fig. 2 ; Fig. 3	-	-	0.8	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 10\text{ ms}$; Fig. 4 ; Fig. 5	-	-	8	A
		half sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 8.3\text{ ms}$	-	-	9	A
T_j	junction temperature		-	-	125	°C
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 10\text{ mA}$; $T_j = 25\text{ °C}$; Fig. 7	-	-	50	μA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 268\text{ V}$; $T_j = 125\text{ °C}$; $R_{GK} = 1\text{ k}\Omega$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; Fig. 12	500	800	-	V/μs
		$V_{DM} = 268\text{ V}$; $T_j = 125\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit; Fig. 12	-	25	-	V/μs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A	anode	 <p>TO-92 (SOT54)</p>	 <p>sym037</p>
2	G	gate		
3	K	cathode		

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BT169D-L	TO92	BT169D-L,116	Reel	2000	SOT54 wide pitch	14-Nov-2013

7. Marking

Table 4. Marking codes

Type number	Marking codes
BT169D-L	BT169DL

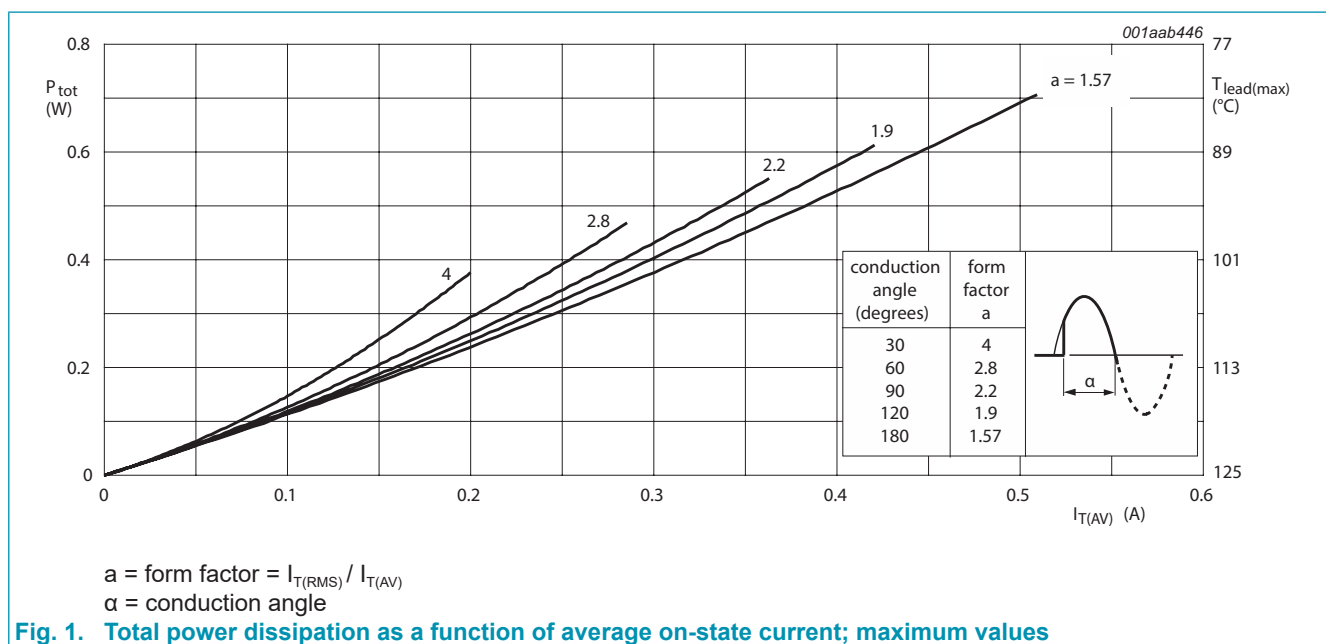
8. Limiting values

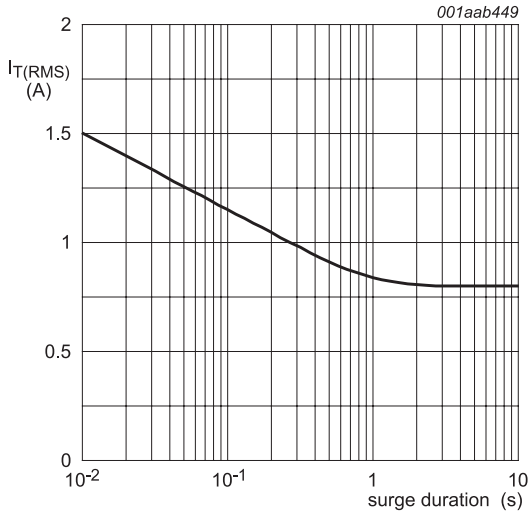
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	400	V
V_{RRM}	repetitive peak reverse voltage		-	400	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{lead} \leq 83\text{ }^{\circ}\text{C}$; Fig. 1	-	0.5	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{lead} \leq 83\text{ }^{\circ}\text{C}$; Fig. 2; Fig. 3	-	0.8	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 10\text{ ms}$; Fig. 4; Fig. 5	-	8	A
		half sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 8.3\text{ ms}$	-	9	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; SIN	-	0.32	A^2s
di_T/dt	rate of rise of on-state current	$I_T = 2\text{ A}$; $I_G = 10\text{ mA}$; $dI_G/dt = 100\text{ mA}/\mu\text{s}$	-	50	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current		-	1	A
V_{RGM}	peak reverse gate voltage		-	5	V
P_{GM}	peak gate power		-	2	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.1	W
T_{stg}	storage temperature		-40	150	$^{\circ}\text{C}$
T_j	junction temperature		[1]	125	$^{\circ}\text{C}$

[1] Operation above 110°C may require the use of a gate to cathode resistor of 1kΩ or less.





$f = 50 \text{ Hz}; T_{\text{lead}} = 83 \text{ }^\circ\text{C}$

Fig. 2. RMS on-state current as a function of surge duration for sinusoidal currents

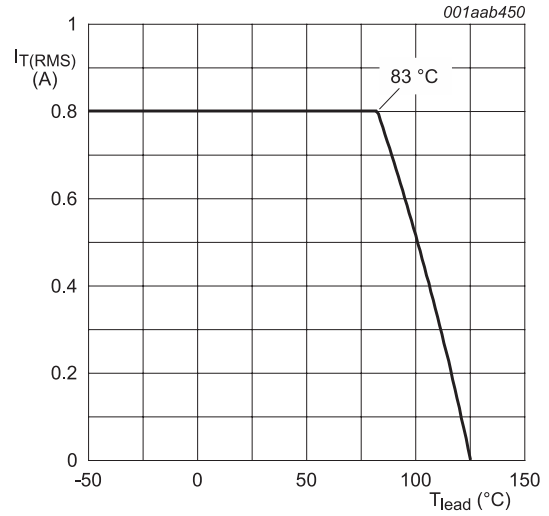
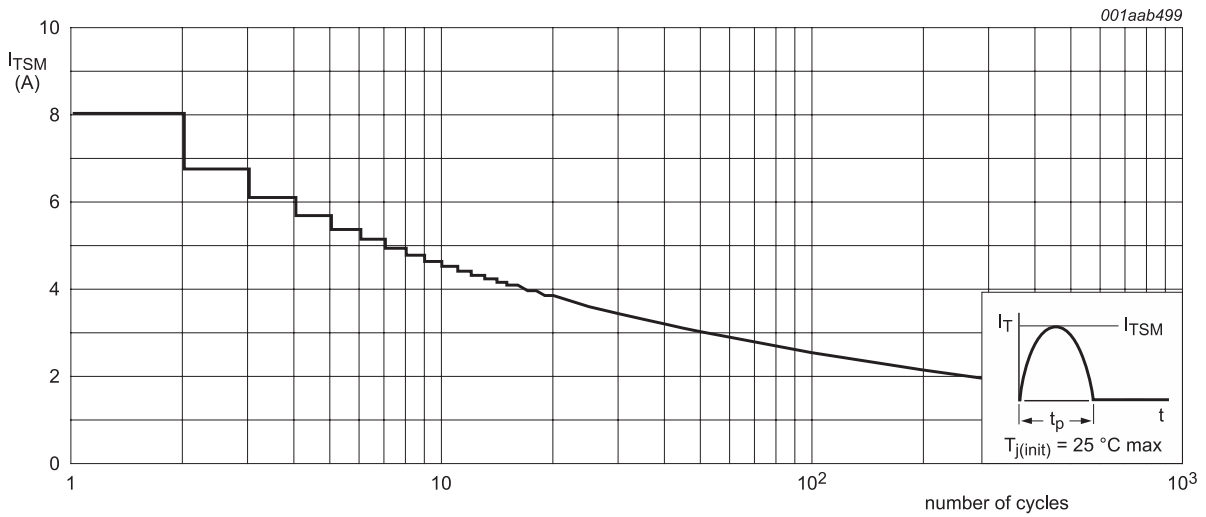
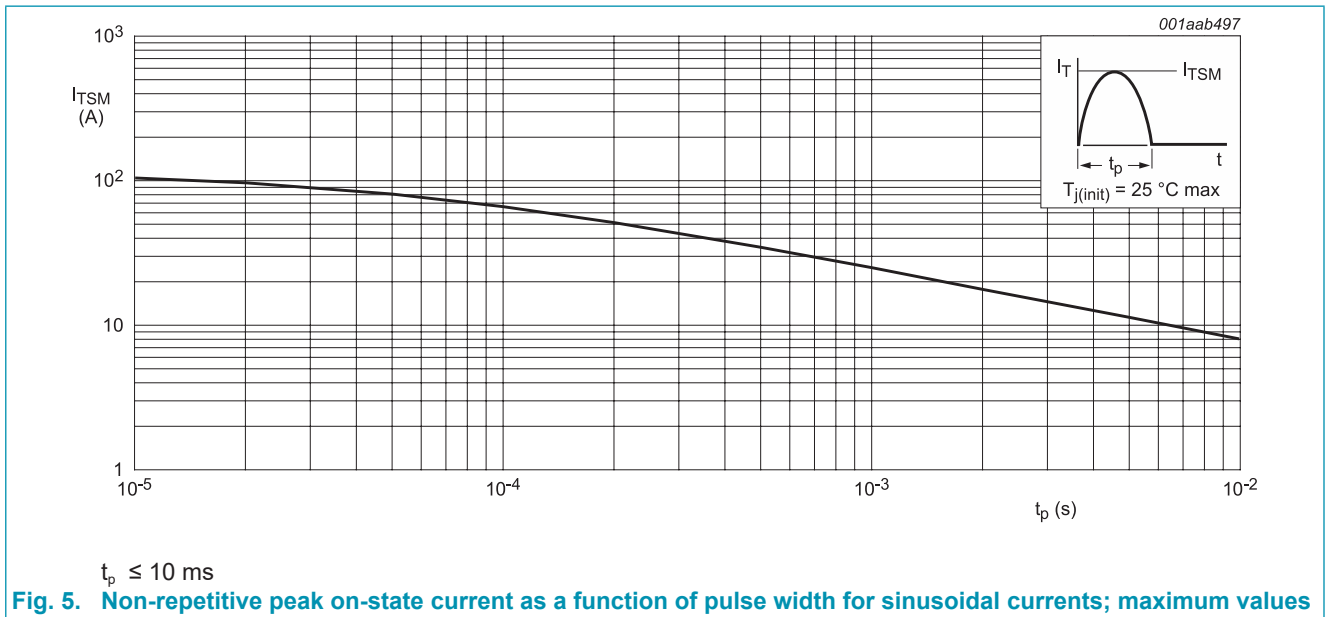


Fig. 3. RMS on-state current as a function of lead temperature; maximum values



$f = 50 \text{ Hz}$

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal currents cycles; maximum values



9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	Fig. 6	-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	printed circuit board mounted: lead length = 4 mm	-	150	-	K/W

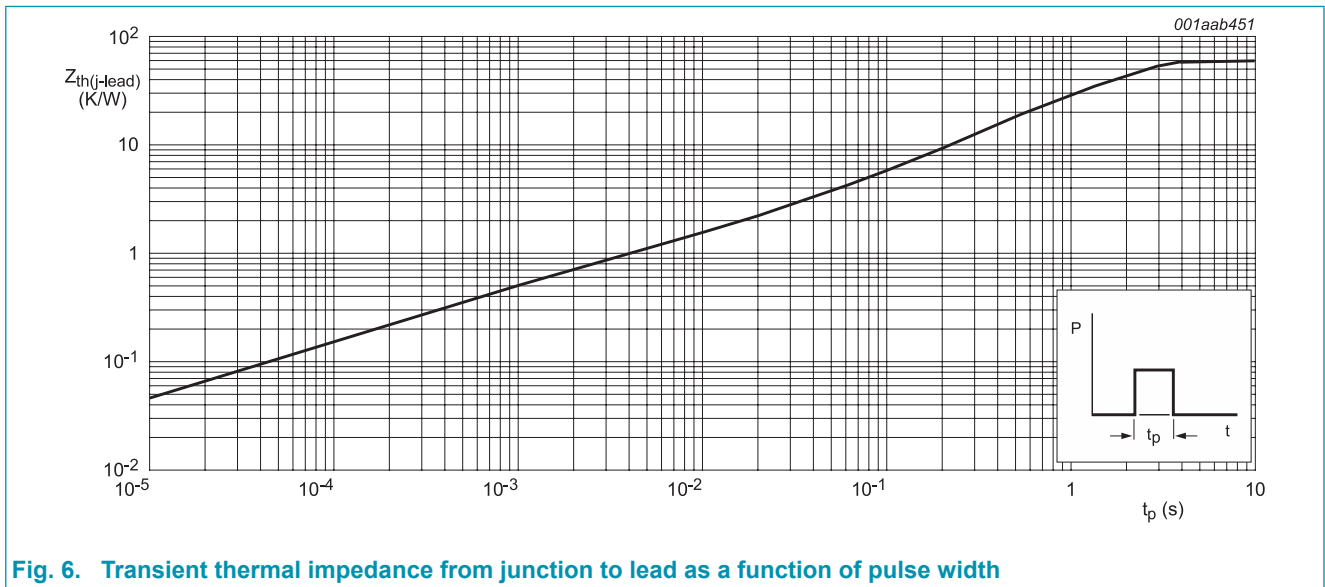


Fig. 6. Transient thermal impedance from junction to lead as a function of pulse width

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 10\text{ mA}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 7	-	-	50	μA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.5\text{ mA}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 8	-	2	4	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 9	-	0.4	1	mA
V_T	on-state voltage	$I_T = 1.2\text{ A}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 10	-	1.25	1.7	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 10\text{ mA}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 11	-	0.5	0.8	V
		$V_D = 12\text{ V}$; $I_T = 10\text{ mA}$; $T_J = 125\text{ }^\circ\text{C}$	0.2	0.3	-	V
I_D	off-state current	$V_D = 400\text{ V}$; $R_{GK} = 1\text{ k}\Omega$; $T_J = 25\text{ }^\circ\text{C}$	-	-	2	μA
		$V_D = 400\text{ V}$; $R_{GK} = 1\text{ k}\Omega$; $T_J = 125\text{ }^\circ\text{C}$	-	0.05	0.1	mA
I_R	reverse current	$V_R = 400\text{ V}$; $T_J = 25\text{ }^\circ\text{C}$; $R_{GK} = 1\text{ k}\Omega$	-	0.05	2	μA
		$V_R = 400\text{ V}$; $T_J = 125\text{ }^\circ\text{C}$; $R_{GK} = 1\text{ k}\Omega$	-	0.05	0.1	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 268\text{ V}$; $T_J = 125\text{ }^\circ\text{C}$; $R_{GK} = 1\text{ k}\Omega$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; Fig. 12	500	800	-	V/ μs
		$V_{DM} = 268\text{ V}$; $T_J = 125\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit; Fig. 12	-	25	-	V/ μs

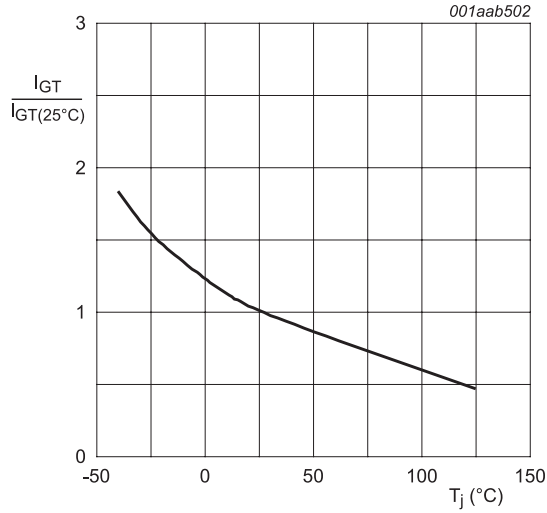
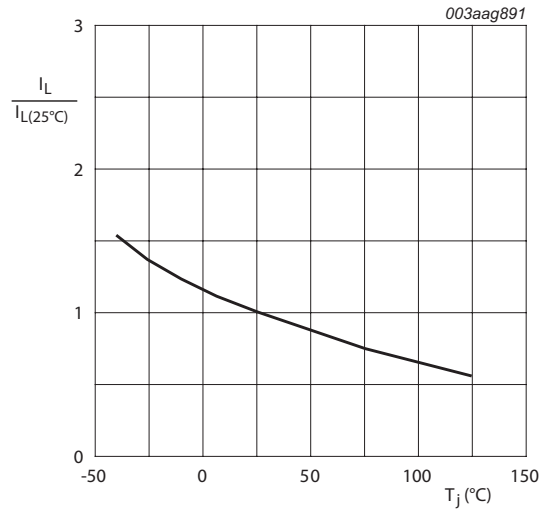
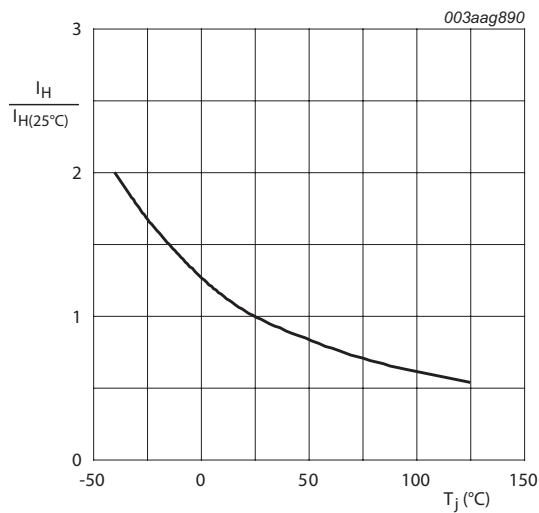


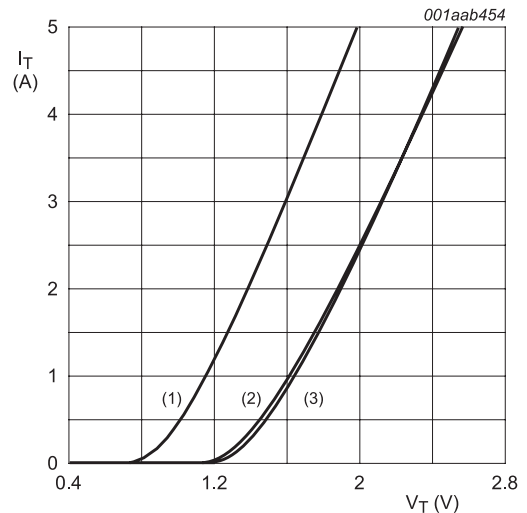
Fig. 7. Normalized gate trigger current as a function of junction temperature



$R_{GK} = 1 \text{ k}\Omega$
Fig. 8. Normalized latching current as a function of junction temperature



$R_{GK} = 1 \text{ k}\Omega$
Fig. 9. Normalized holding current as a function of junction temperature



$V_o = 1.067 \text{ V}; R_s = 0.187 \Omega$
(1) $T_j = 125 \text{ }^\circ\text{C}$; typical values
(2) $T_j = 125 \text{ }^\circ\text{C}$; maximum values
(3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values
Fig. 10. On-state current as a function of on-state voltage

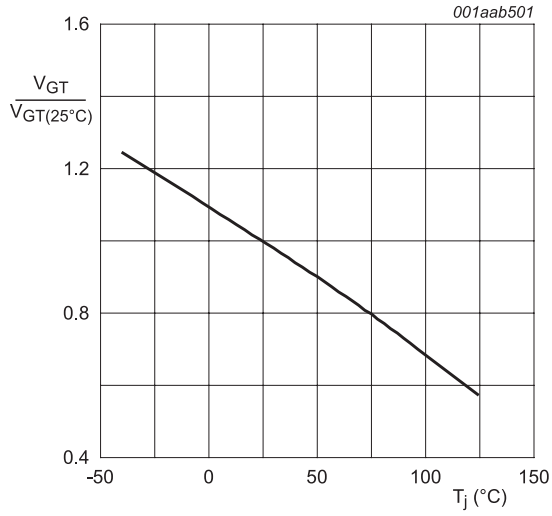
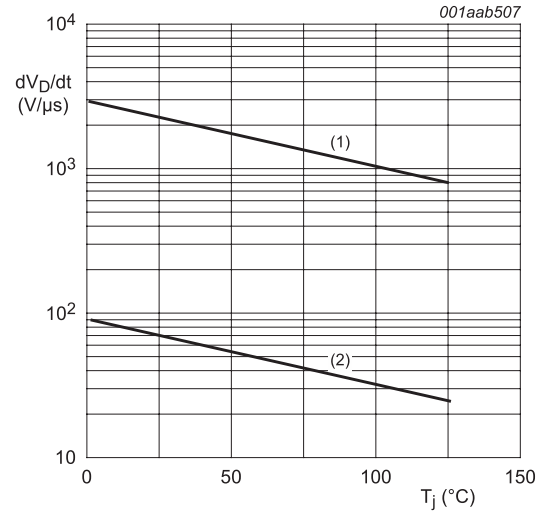


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

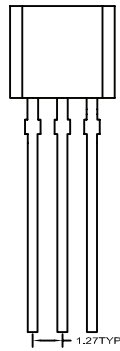


(1) $R_{GK} = 1 \text{ k}\Omega$;
 (2) gate open circuit

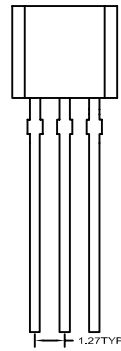
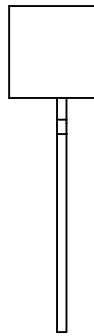
Fig. 12. Critical rate of rise of off-state voltage as a function of junction temperature; typical values

11. Package outline

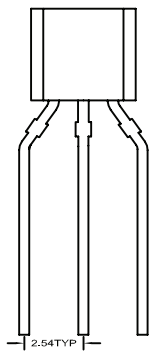
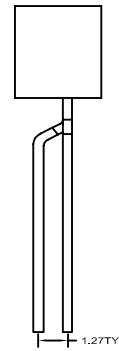
SOT54 PACKAGE OUTLINE



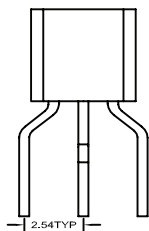
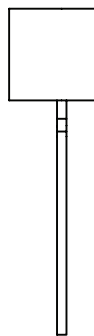
SOT54
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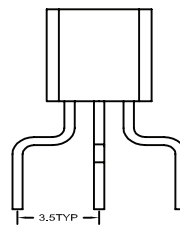
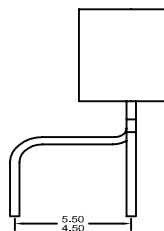
SOT54 LEADS ON CIRCLE
Bulk Pack - 112



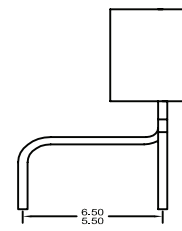
SOT54 WIDE PITCH
Tape/ Reel Pack - 116
Ammo Pack - 126



SOT54 LEAD BEND L01
Bulk Pack - 412



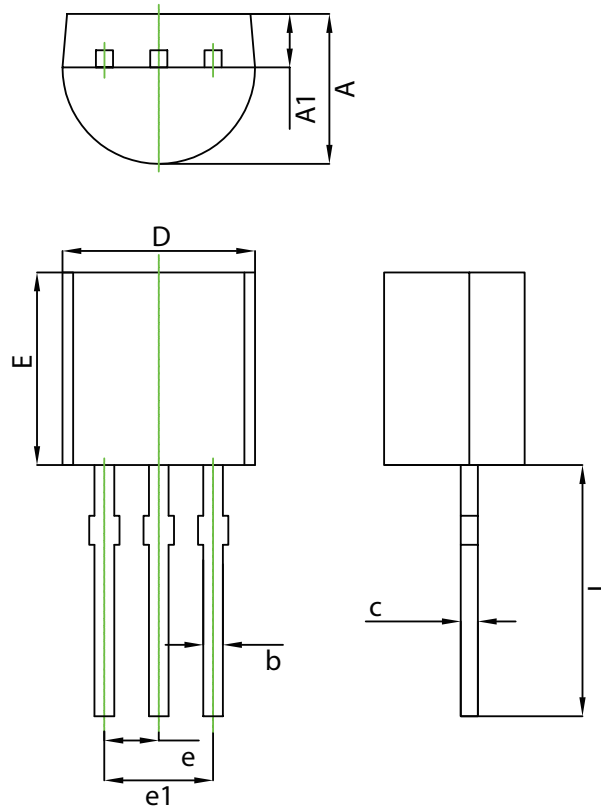
SOT54 LEAD BEND L02
Bulk Pack - 412



Remark: Detailed dimensions refer to POD drawing.

Plastic single-ended leaded(through hole) package; 3 leads

TO92



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.300	4.700	0.169	0.185
E	4.300	4.700	0.169	0.185
e	1.270 TYP.		0.050 TYP.	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571

12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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